1-bit to 2-bit Address Driver with 3-state Outputs

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ADE-205-198 (Z) Preliminary 1st. Edition November 1997

Description

This 1-bit to 2-bit address driver is designed for 2.3 V to 3.6 V V_{cc} operation. To ensure the high impedance state during power up or power down, the output ebable (\overline{OE}) input should be tied to V_{cc} through a pullup resistor; the minimum value of the resistor is determined by the current sinking capability of the driver.

Features

- $V_{cc} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current ± 24 mA (@V_{cc} = 3.0 V)

Function Table

Inputs			Outputs	
OE1	OE2	Α	1Yn	2Yn
L	Н	Н	Н	Z
L	Н	L	L	Z
Н	L	Н	Z	Н
Н	L	L	Z	L
L	L	Н	Н	Н
L	L	L	L	L
Н	Н	X	Z	Z

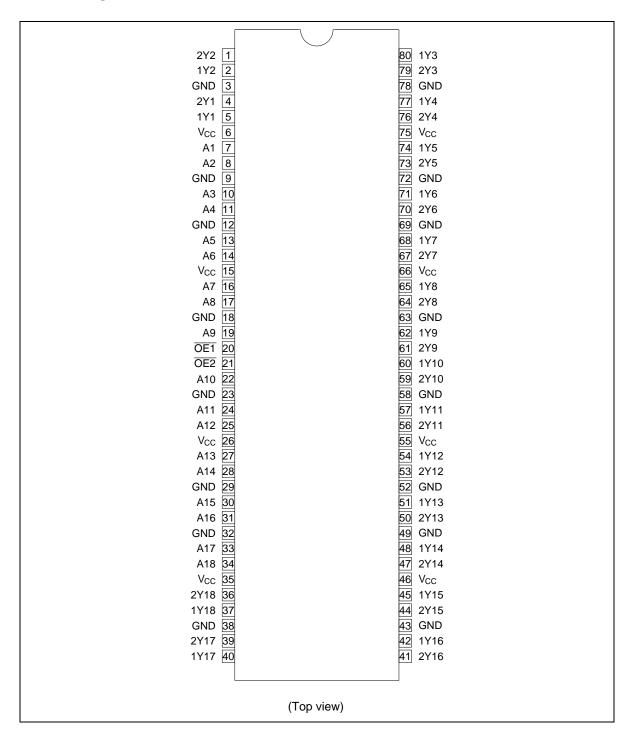
H: High level

L : Low level

X: Immaterial

Z: High impedance

Pin Arrangement



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Absolute Maximum Ratings

Item	Symbol		Unit	Conditions
Supply voltage	V _{cc}	-0.5 to 4.6	V	
Input voltage *1	V,	-0.5 to 4.6	V	
Output voltage *1,2	V _o	–0.5 to V _{cc} +0.5	V	
Input clamp current	I _{IK}	- 50	mA	V ₁ < 0
Output clamp current	I _{ok}	±50	mA	$V_o < 0 \text{ or } V_o > V_{cc}$
Continuous output current	Io	±50	mA	$V_o = 0$ to V_{cc}
V _{cc} , GND current / pin	I _{cc} or I _{GND}	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) ^{'3}	P _T	1	W	TVSOP
Storage temperature	T_{stg}	-65 to 150	°C	

Notes:

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

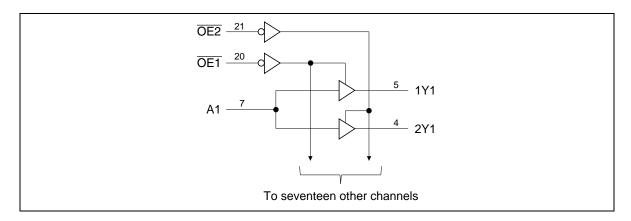
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V _{cc}	2.3	3.6	V	
Input voltage	V _I	0	V _{cc}	V	
Output voltage	V _o	0	V _{cc}	V	
High level output current	I _{OH}	_	-12	mA	V _{cc} = 2.3 V
		_	-12		V _{cc} = 2.7 V
		_	-24		$V_{cc} = 3.0 \text{ V}$
Low level output current	I _{oL}	_	12	mA	V _{cc} = 2.3 V
		_	12		V _{cc} = 2.7 V
		_	24		V _{cc} = 3.0 V
Input transition rise or fall rate	Æt / Æv	0	10	ns / V	
Operating temperature	T _a	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



Electrical Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

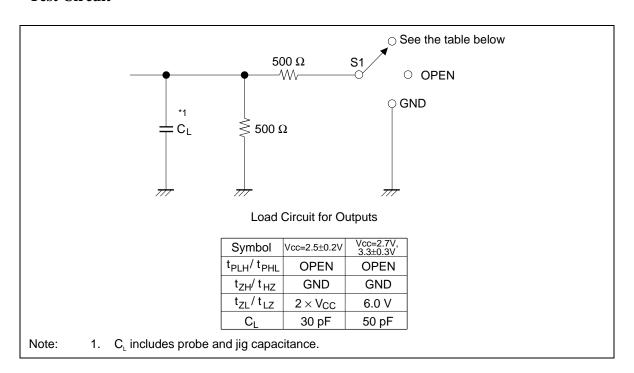
Item	Symbol	V _{cc} (V)	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_		
	V _{IL}	2.3 to 2.7	_	0.7	_	
		2.7 to 3.6	_	0.8	_	
Output voltage	V _{OH}	2.3 to 3.6	V _{cc} -0.2	_	V	$I_{OH} = -100 \mu A$
		2.3	2.0	_		$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.3	1.7	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.7	2.2	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.4	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	_		$I_{OH} = -24 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V _{oL}	2.3 to 3.6	_	0.2		$I_{OL} = 100 \mu A$
		2.3	_	0.4	_	$I_{OL} = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3	_	0.7		$I_{OL} = 12 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.7	_	0.4		$I_{OL} = 12 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		3.0	_	0.55	_	$I_{OL} = 24 \text{ mA}, V_{IL} = 0.8 \text{ V}$
Input current	I _{IN}	3.6	_	±5	μΑ	$V_{IN} = V_{CC}$ or GND
Off state output current	l _{oz}	3.6	_	±10	μΑ	$V_{OUT} = V_{CC}$ or GND
Quiescent supply current	I _{cc}	3.6	_	40	μА	$V_{IN} = V_{CC}$ or GND
	ΔI_{cc}	3.0 to 3.6	_	750	μΑ	V_{IN} = one input at (V_{CC} -0.6) V, other inputs at V_{CC} or GND

Switching Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH}	2.5±0.2	1.0	_	3.8	ns	Α	Υ
	$t_{\scriptscriptstylePHL}$	2.7	_	_	3.8			
		3.3±0.3	1.0	_	3.0			
Output enable time	t _{zH}	2.5±0.2	1.0	_	5.4	ns	ŌĒ	Υ
	$\mathbf{t}_{\scriptscriptstyle ZL}$	2.7	_	_	5.4			
		3.3±0.3	1.0	_	4.4			
Output disable time	t _{HZ}	2.5±0.2	1.0	_	5.4	ns	ŌĒ	Υ
	$\mathbf{t}_{\scriptscriptstyle{LZ}}$	2.7	_	_	4.6			
		3.3±0.3	1.0	_	4.1			
Input capacitance	C _{IN}	3.3	_	4.5	_	pF	Control in	nputs
		3.3	_	5.0	_		Data inpu	ıts
Output capacitance	C _o	3.3	_	7.5	_	pF		

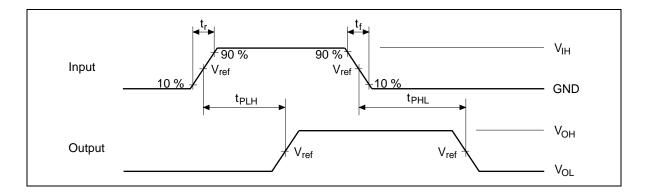
Test Circuit

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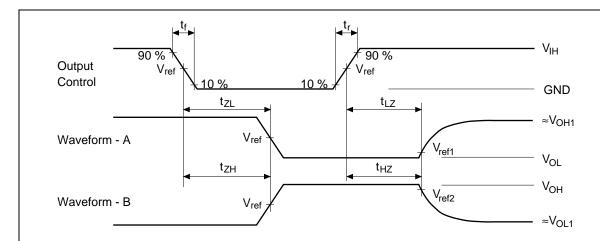


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Waveforms - 1



Waveforms - 2



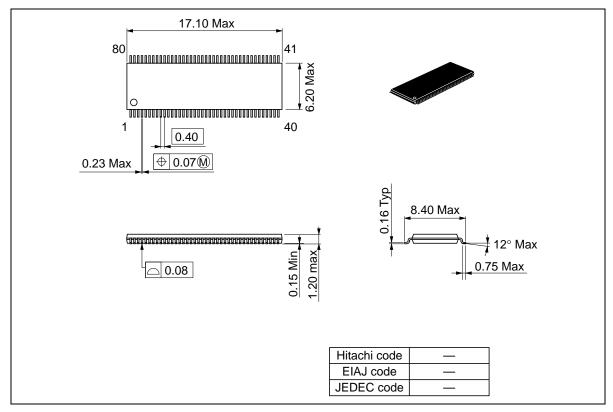
TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
V_{IH}	V _{CC}	2.7 V
V_{ref}	1/2 V _{CC}	1.5 V
V _{ref1}	V _{OL} +0.15 V	V _{OL} +0.3 V
V _{ref2}	V _{OH} -0.15 V	V _{OH} -0.3 V
V _{OH1}	V _{CC}	3.0 V
V _{OL1}	GND	GND

Notes:

- 1. All input pulses are supplied by generators having the following characteristics : PRR \leq 10 MHz, Zo = 50 $\Omega,\,t_{_{f}}\leq$ 2.0 ns, $t_{_{f}}\leq$ 2.0 ns. (V $_{_{CC}}$ = 2.5±0.2 V) PRR \leq 10 MHz, Zo = 50 $\Omega,\,t_{_{f}}\leq$ 2.5 ns, $t_{_{f}}\leq$ 2.5 ns. (V $_{_{CC}}$ = 2.7 V, 3.3±0.3 V)
- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions

Unit: mm



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